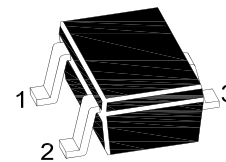
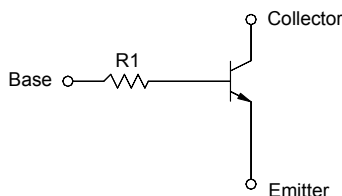


NPN Silicon Epitaxial Planar Digital Transistor



1.Base 2.Emitter 3.Collector
SOT-523 Plastic Package

Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	V_{CBO}	50	V
Collector Emitter Voltage	V_{CEO}	50	V
Emitter Base Voltage	V_{EBO}	5	V
Collector Current	I_C	100	mA
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Typ.	Max.	Unit
DC Current Gain at $V_{CE} = 5\text{ V}$, $I_C = 1\text{ mA}$	h_{FE}	100	-	600	-
Collector Base Cutoff Current at $V_{CB} = 50\text{ V}$	I_{CBO}	-	-	500	nA
Emitter Base Cutoff Current at $V_{EB} = 4\text{ V}$	I_{EBO}	-	-	500	nA
Collector Base Breakdown Voltage at $I_C = 50\text{ }\mu\text{A}$	$V_{(BR)CBO}$	50	-	-	V
Collector Emitter Breakdown Voltage at $I_C = 1\text{ mA}$	$V_{(BR)CEO}$	50	-	-	V
Emitter Base Breakdown Voltage at $I_E = 50\text{ }\mu\text{A}$	$V_{(BR)EBO}$	5	-	-	V
Collector Emitter Saturation Voltage at $I_C = 5\text{ mA}$, $I_B = 0.25\text{ mA}$	$V_{CE(sat)}$	-	-	0.3	V
Input Resistance	R_1	3.29	4.7	6.11	K Ω
Transition Frequency at $V_O = 10\text{ V}$, $I_O = 5\text{ mA}$, $f = 100\text{ MHz}$	f_T	-	250	-	MHz

MMDTC143TE

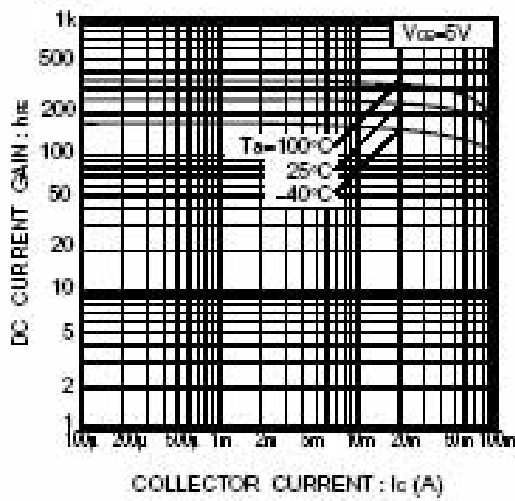


Fig.1 DC current gain vs. collector current

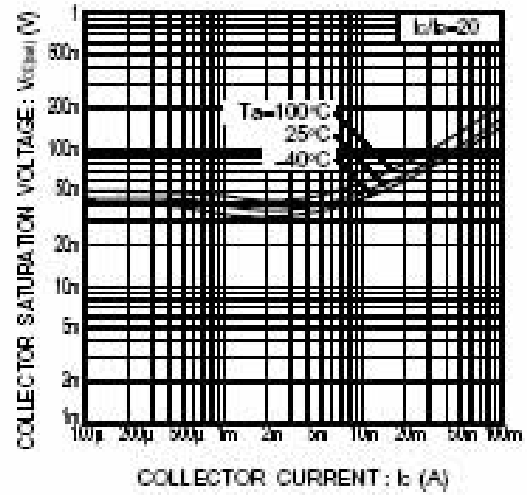


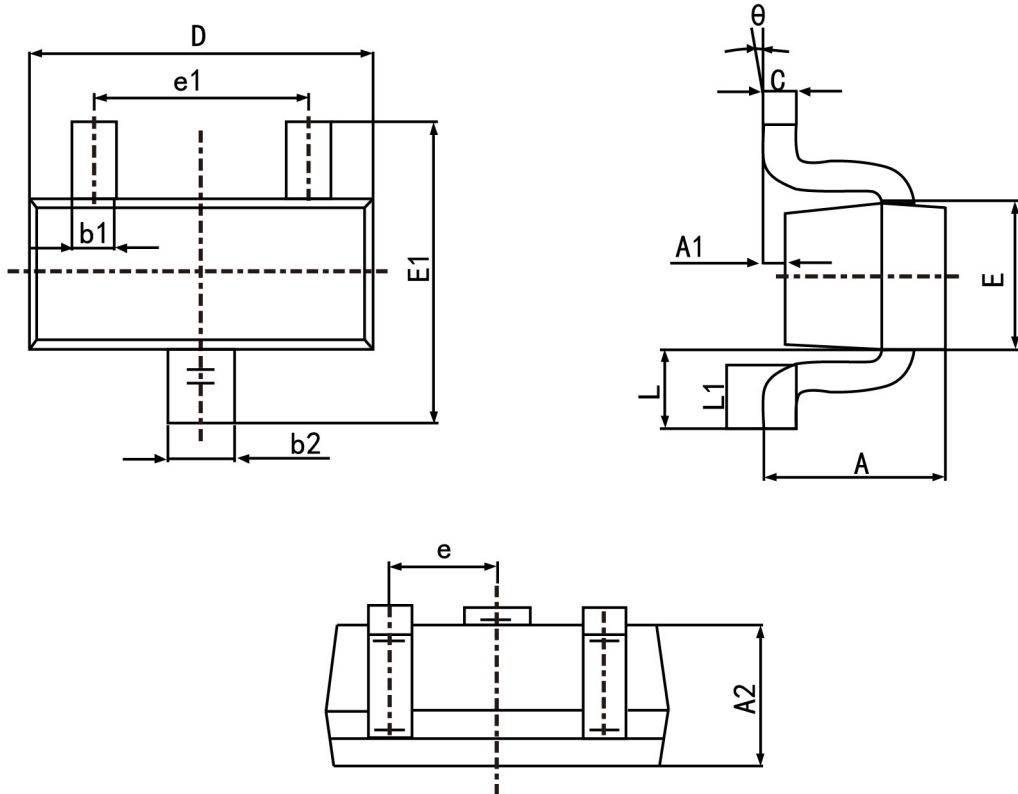
Fig.2 Collector-emitter saturation voltage vs. collector current



PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT-523



Symbol	Dimension in Millimeters	
	Min	Max
A	0.700	0.900
A1	0.000	0.100
A2	0.700	0.800
b1	0.150	0.250
b2	0.250	0.350
c	0.100	0.200
D	1.500	1.700
E	0.700	0.900
E1	1.450	1.750
e	0.500	TYP.
e1	0.900	1.100
L	0.400 REF.	
L1	0.260	0.460
θ	0°	8°